AMENDMENT

IN THE CLAIMS

Please replace claims 1, 8 and 13 with the following re-written clean versions.

1. (Amended) An organic electroluminescence device comprising:

an organic electroluminescence element and a thin film transistor which are formed on a substrate; said organic electroluminescence element having at least an organic emissive layer disposed between an anode and a cathode; said thin film transistor controlling a current flowing to said organic electroluminescence element; said thin film transistor having an active layer made of a semiconductor material; and

a refractory metal layer connecting a source region or drain region of said thin film transistor to said anode of said organic electroluminescence element, said refractory metal layer, one of said source region and drain region, and said anode being laminated in a thickness direction of said substrate.

8. (Amended) An organic electroluminescence device comprising:

pixels, each of said pixels including an organic electroluminescence element and a thin film transistor, said organic electroluminescence element having an emissive layer disposed between an anode and a cathode, said thin film transistor controlling a current flowing from a power source line to said organic electroluminescence element, said thin film transistor having an active layer made of a semiconductor material; and

a contact between one of a source and drain in said active layer and said anode of said organic electroluminescence element, and between the other of said source and drain

in said active layer and said power source line, said contact being achieved through a refractory metal layer, said refractory metal layer, one of said source and drain, and said anode being laminated in a thickness direction of said organic electroluminescence device.

13. (Amended) A light emitting device comprising:

an emissive element having an emissive layer between a first electrode and a second electrode;

a thin film transistor for controlling power supplied to said emissive element, said thin film transistor having an active layer made of a semiconductor material; and

a refractory metal layer connecting a first electrode region in said active layer to said first electrode of said emissive element, said refractory metal layer, said first electrode region and said first electrode being laminated in a thickness direction of said light emitting device.

Please enter the following newly added claims 20-22.

20. (Newly Added) The device defined in Claim 1, further comprising a planarizing film on which said anode is formed.

21. (Newly Added) The display device defined in Claim 8, further comprising a planarizing film on which said anode is formed.

22. (Newly Added) The light emitting device defined in Claim 13, further comprising a planarizing film on which said anode is formed.